

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Nevin et al.

GROUP: 2818

SERIAL NO: 10/727,449

EXAMINER: Phuc T. Dang

FILED: December 4, 2003

FOR: **METHOD OF FORMING A CAVITY AND SOI IN A
SEMICONDUCTOR SUBSTRATE (As Now Amended)**

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

AMENDMENT

In response to the Office Action mailed April 13, 2005, please amend the above-identified application as indicated on the attached sheets.